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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

S. KONDO et al

Serial No. 09/637,570 Group Art Unit: 2812

Filed: August 14, 2000 Examiner: Ha T. Nguyen

For: POLISHING METHOD, METALLIZATION FABRICATION  
METHOD, METHOD FOR MANUFACTURING SEMICONDUCTOR  
DEVICE AND SEMICONDUCTOR DEVICE

AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated April 24, 2002,  
please amend the above-identified application as follows:

IN THE CLAIMS

Cancel claims 22 and 23 without prejudice or disclaimer,  
and rewrite claims 1, 6, 9, 13, 14, 16, 17, 19, and 20 as  
follows:

1. (Amended) A polishing method for a copper film by  
chemical mechanical polishing, comprising forming a  
protection-layer with a forming agent, polishing the  
protection-layer away on a convex portion of the copper film,  
oxidizing a surface of the convex portion of the copper film